

RoHS

COMPLIANT HALOGEN

FREE

RSM2302N-VB Datasheet

N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A) ^e	Q _g (Typ.)		
	0.028 at V _{GS} = 4.5 V	6 ^a			
20	0.042 at V _{GS} = 2.5 V	6 ^a	8.8 nC		
	0.050 at V _{GS} = 1.8 V	5.6			

SOT-23

D 3

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % Rg Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- DC/DC Converters
- Load Switch for Portable Applications

Top View					
ABSOLUTE MAXIMUM RATIN	I GS T₄ = 25 °C,	unless otherv	vise noted		
Parameter	, A start st	Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	20	v	
Gate-Source Voltage		V _{GS}	± 12	V	
	T _C = 25 °C		6 ^a		
Continuous Drain Consent (T. 150 °C)	T _C = 70 °C	1. [5.1		
Continuous Drain Current ($T_J = 150 \ ^{\circ}C$)	T _A = 25 °C		5 ^{b, c}		
	T _A = 70 °C	1	4 ^{b, c}	A	
Pulsed Drain Current		I _{DM}	20		
Continuous Source-Drain Diode Current	T _C = 25 °C		1.75		
Commuous Source-Drain Diode Current	T _A = 25 °C	I _S	1.04 ^{b, c}		
	T _C = 25 °C		2.1		
Maximum Dawar Dissinction	T _C = 70 °C		1.3	w	
Maximum Power Dissipation	T _A = 25 °C	P _D	1.25 ^{b, c}	vv	
	T _A = 70 °C	1 –	0.8 ^{b, c}		
Operating Junction and Storage Temperature	e Range	T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Tempera	ature)		260		

THERMAL RESISTANCE RATINGS							
Parameter		Symbol	Typical	Maximum	Unit		
Maximum Junction-to-Ambient ^{b, d}	t ≤ 5 s	R _{thJA}	80	100	°C/W		
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	40	60	0/11		

Notes:

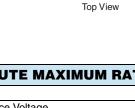
a. Package limited

b. Surface Mounted on 1" x 1" FR4 board.

c. t = 5 s.

d. Maximum under steady state conditions is 125 °C/W.

e. Based on T_C = 25 °C.



G 1

s 2

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static					•		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$	20			V	
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	L = 250 µA		25		mV/°C	
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I _D = 250 μA		- 2.6			
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \ \mu A$	0.45		1.0	V	
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 8 V$			± 100	nA	
	I _{DSS}	$V_{DS} = 20 V, V_{GS} = 0 V$			1	μΑ	
Zero Gate Voltage Drain Current		V_{DS} = 20 V, V_{GS} = 0 V, T_{J} = 70 °C			10		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le 5$ V, V_{GS} = 4.5 V	20			Α	
		$V_{GS} = 4.5 \text{ V}, I_D = 5.0 \text{ A}$		0.028			
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 4.7 \text{ A}$		0.042		Ω	
		$V_{GS} = 1.8 \text{ V}, I_D = 4.3 \text{ A}$		0.050			
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 5.0 A		24		S	
Dynamic ^b	<u> </u>			•	<u>1</u>		
Input Capacitance	C _{iss}			865		pF	
Output Capacitance	C _{oss}	V _{DS} = 10 V, V _{GS} = 0 V, f = 1 MHz		105			
Reverse Transfer Capacitance	C _{rss}			55			
-		$V_{DS} = 10 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 5.0 \text{ A}$		12	18	1	
Total Gate Charge	Qg			8.8	14	nC	
Gate-Source Charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 5.0 \text{ A}$		1.1			
Gate-Drain Charge	Q _{gd}			0.7			
Gate Resistance	Rg	f = 1 MHz	0.5	2.4	4.8	Ω	
Turn-On Delay Time	t _{d(on)}			8	16	-	
Rise Time	t _r	V_{DD} = 10 V, R_L = 2.2 Ω		17	26		
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D} \cong \text{4}$ A, V_GEN = 4.5 V, R_g = 1 Ω		31	47		
Fall Time	t _f			8	16	ns	
Turn-On Delay Time	t _{d(on)}			5	10	115	
Rise Time	t _r	V_{DD} = 10 V, R_L = 2.2 Ω	-	13	20	-	
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong \text{4}$ A, V_GEN = 5 V, R_g = 1 Ω	-	21	32		
Fall Time	t _f		-	6	12	-	
Drain-Source Body Diode Characteristic	s		Į		<u> </u>	<u>I</u>	
Continuous Source-Drain Diode Current	ا _S	T _C = 25 °C			1.75		
Pulse Diode Forward Current	I _{SM}				20	A	
Body Diode Voltage	V _{SD}	$I_{S} = 4 A, V_{GS} = 0 V$		0.75	1.2	V	
Body Diode Reverse Recovery Time	t _{rr}		1	12	20	ns	
Body Diode Reverse Recovery Charge	Q _{rr}			5	10	nC	
Reverse Recovery Fall Time	t _a	$I_F = 4 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, \text{ T}_J = 25 ^\circ\text{C}$		7			
Reverse Recovery Rise Time	t _b			5		ns	

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 % b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



- 55 °C

1.5

20

T_C =

15

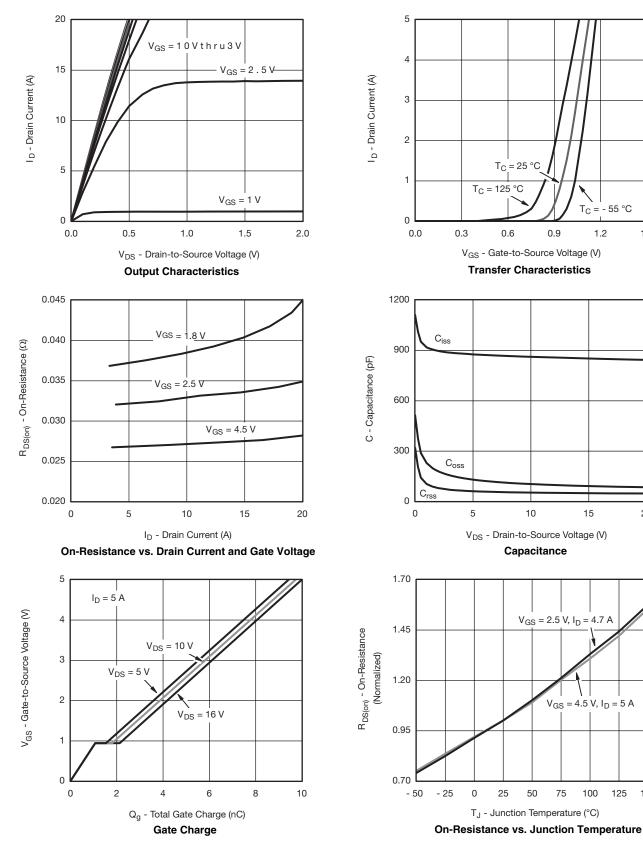
75

100

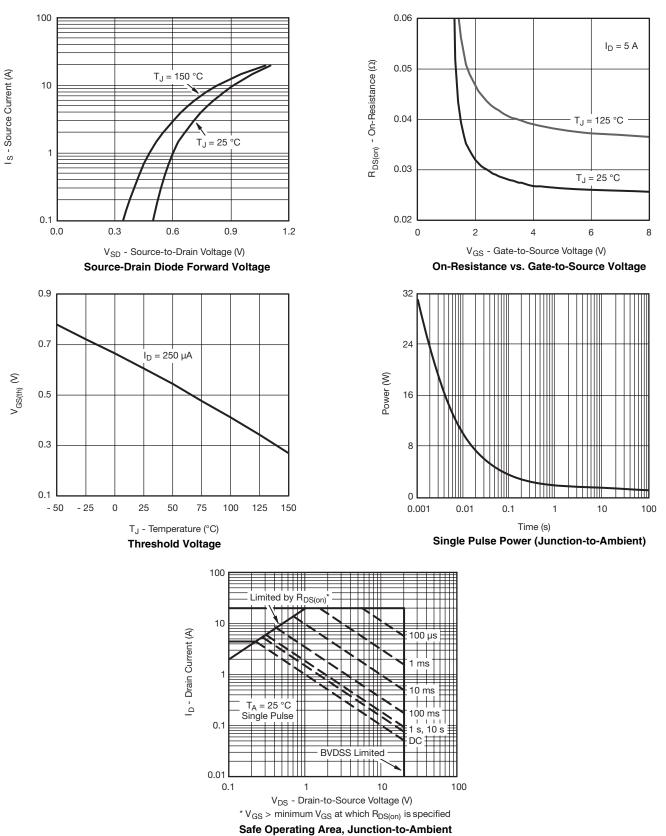
125 150

1.2

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted







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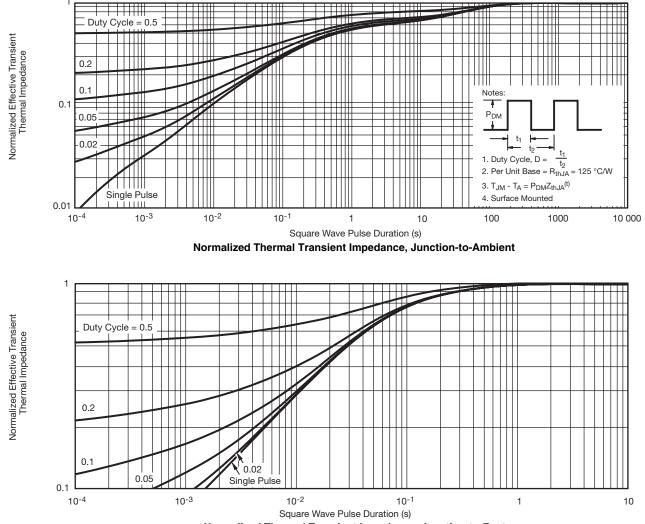
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



* The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot



SOT-23 (TO-236): 3-LEAD







Dim	MILLIN	IETERS	INCHES		
	Min	Мах	Min	Max	
Α	0.89	1.12	0.035	0.044	
A ₁	0.01	0.10	0.0004	0.004	
A ₂	0.88	1.02	0.0346	0.040	
b	0.35	0.50	0.014	0.020	
С	0.085	0.18	0.003	0.007	
D	2.80	3.04	0.110	0.120	
E	2.10	2.64	0.083	0.104	
E ₁	1.20	1.40	0.047	0.055	
е	0.95 BSC		0.0374 Ref		
e ₁	1.90 BSC		0.0748 Ref		
L	0.40	0.60	0.016	0.024	
L ₁	0.64 Ref		0.025 Ref		
S	0.50 Ref		0.020 Ref		
q	3°	8°	3°	8°	
ECN: S-03946-Rev. K, 09-Jul-01 DWG: 5479					



RECOMMENDED MINIMUM PADS FOR SOT-23



Recommended Minimum Pads Dimensions in Inches/(mm)



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